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November 2013

## **FQP17N40**

# N-Channel QFET $^{\circledR}$ MOSFET 400 V, 16 A, 270 m $\Omega$

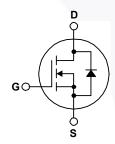
## **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### **Features**

- 16 A, 400 V,  $R_{DS(on)}$  = 270 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 8.0 A
- Low Gate Charge (Typ. 45 nC)
- Low Crss (Typ. 30 pF)
- · 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP17N40	Unit
V <sub>DSS</sub>	Drain-Source Voltage		400	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		16	Α
	- Continuous (T <sub>C</sub> = 100°C)		10.1	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	64	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	16	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	17	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		170	W
	- Derate above 25°C		1.35	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

## **Thermal Characteristics**

Symbol	Parameter	FQP17N40	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.74	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP17N40	FQP17N40	TO-220	Tube	N/A	N/A	50 units

## **Electrical Characteristics**

Symbol	Parameter	Test Conditions		Тур	Max	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	400			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		0.44		V/°C
I <sub>DSS</sub>	s s	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 320 V, T <sub>C</sub> = 125°C			10	μΑ	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics			1		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.0 A		0.21	0.27	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 8.0 A		13		S
C <sub>iss</sub>	Input Capacitance Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1800 270	2300 350	pF pF
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0  MHz		1800	2300	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			30	40	pF
	ing Characteristics				I	
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD}$ = 200 V, $I_{D}$ = 17.2 A, $R_{G}$ = 25 $\Omega$ (Note 4)		40	90	ns
t <sub>r</sub>	Turn-On Rise Time			185	380	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			90	190	ns
t <sub>f</sub>	Turn-Off Fall Time	` ,	/	105	220	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 320 \text{ V}, I_D = 17.2 \text{ A},$ $V_{GS} = 10 \text{ V}$		45	60	nC
Q <sub>gs</sub>	Gate-Source Charge			11.4		nC
( )	Gate-Drain Charge	(Note 4)		21.7		nC
<b>⊄</b> gd						
	Source Diode Characteristics ar	nd Maximum Ratings				
Drain-S	Source Diode Characteristics at  Maximum Continuous Drain-Source Dio				16	A
Q <sub>gd</sub> Drain-S I <sub>S</sub> I <sub>SM</sub>		ode Forward Current			16 64	A

## $Q_{rr}$

 $t_{rr}$ 

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 6.8 mH, I $_{AS}$  = 16 A, V $_{DD}$  = 50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C. 3. I $_{SD}$   $\leq$  17.2 A, di/dt  $\leq$  200 A/ $_{\mu S}$ , V $_{DD}$   $\leq$  BV $_{DSS}$ , starting T $_{J}$  = 25°C. 4.Essentially independent of operating temperature.

Reverse Recovery Time

Reverse Recovery Charge

ns

μС

290

2.5

 $V_{GS} = 0 \text{ V}, I_{S} = 17.2 \text{ A},$ 

 $dI_F / dt = 100 A/\mu s$ 

## **Typical Characteristics**

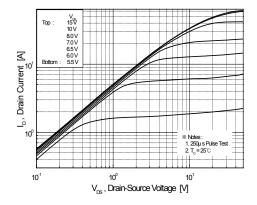


Figure 1. On-Region Characteristics

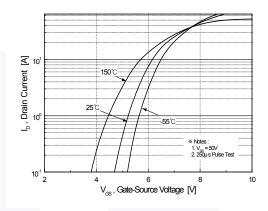


Figure 2. Transfer Characteristics

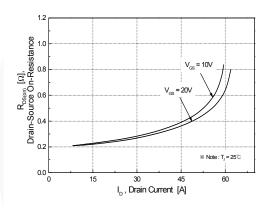


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

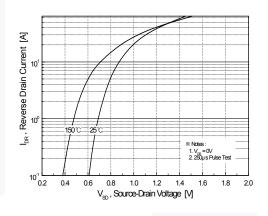


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

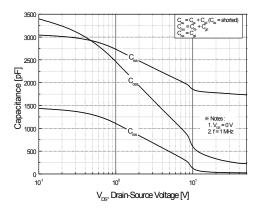


Figure 5. Capacitance Characteristics

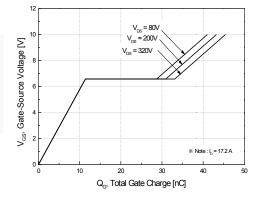
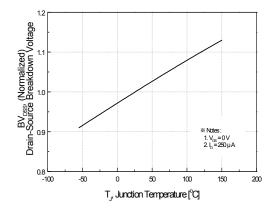


Figure 6. Gate Charge Characteristics

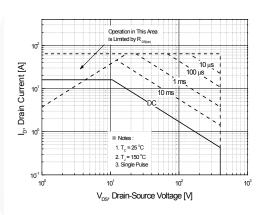
## Typical Characteristics (continued)



30 25 (pagingular) 20 25 (paging

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



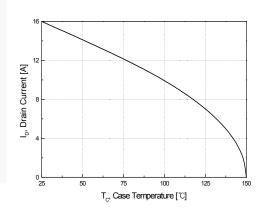


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

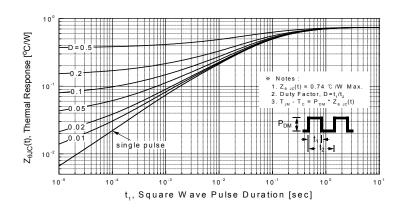


Figure 11. Transient Thermal Response Curve

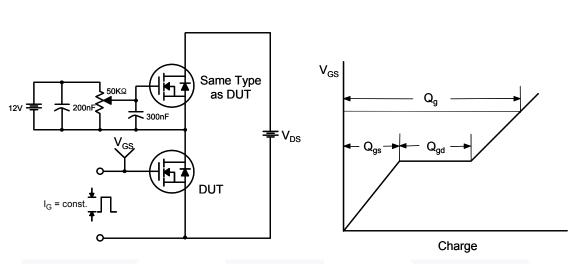


Figure 12. Gate Charge Test Circuit & Waveform

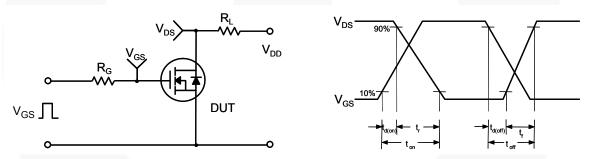


Figure 13. Resistive Switching Test Circuit & Waveforms

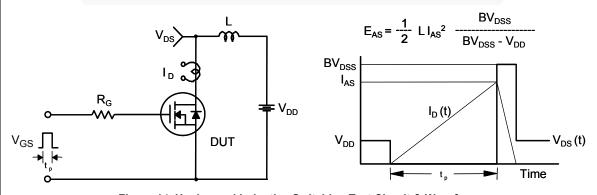
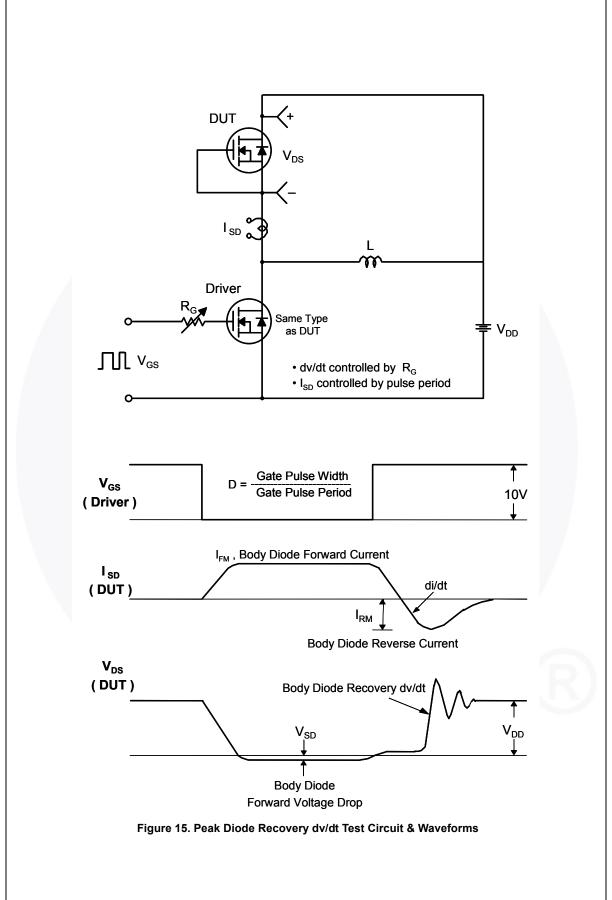
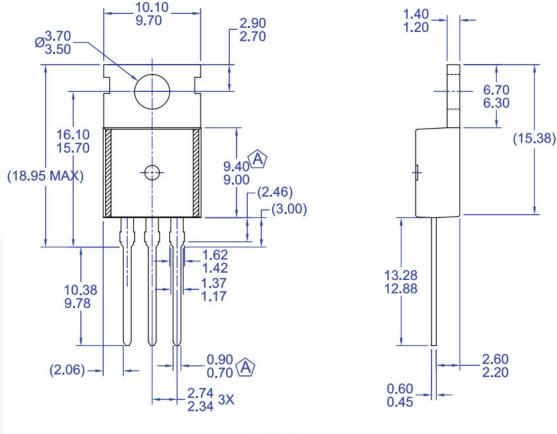


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**



4.70 4.30

9.80

### NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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